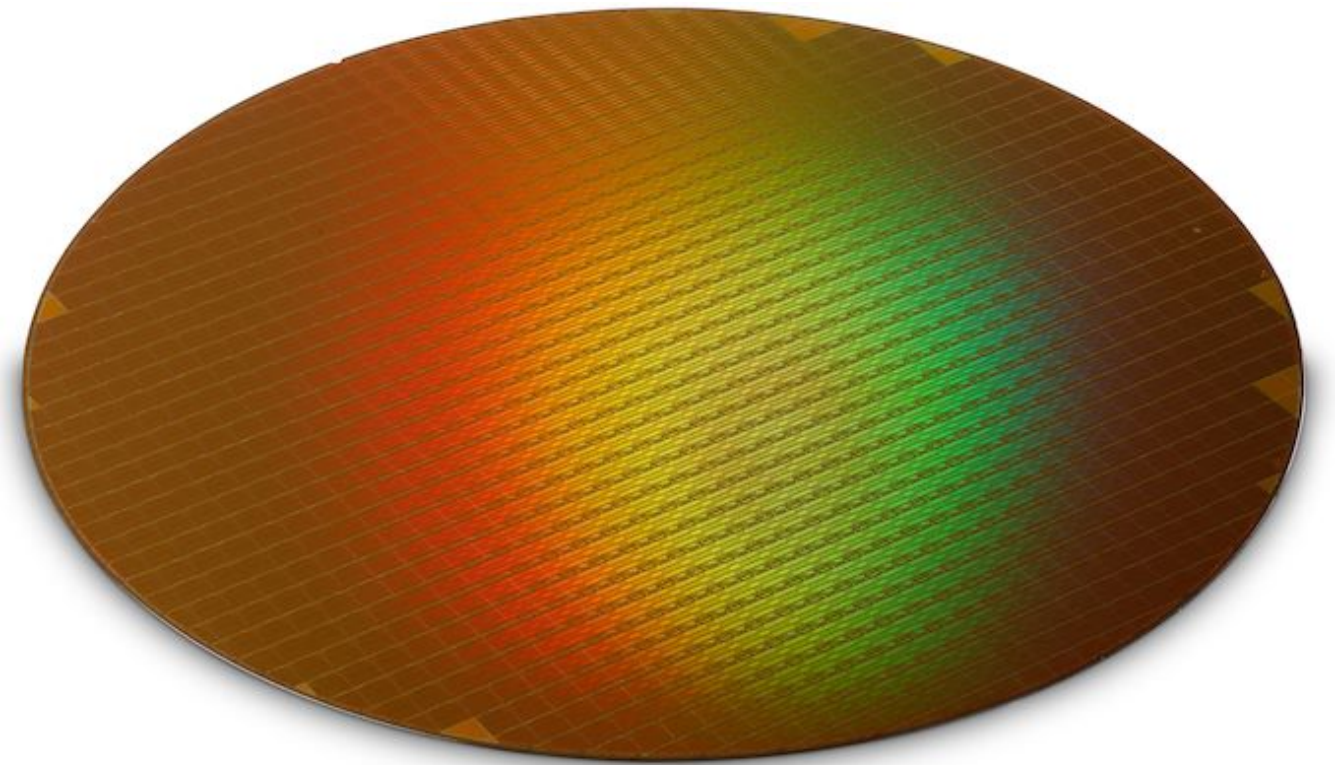


Micron Produces DRAM With 1z Nanometer Process

Written by Alice Marshall
21 August 2019

Micron claims it is the first company to start mass production of 16Gb DDR4 and LPDDR4X memory products using 3rd Generation 10 nm-class fabrication technology, also known as 1z nanometer.



“Development and mass production of the industry’s smallest feature size DRAM node are a testament to Micron’s world-class engineering and manufacturing capabilities, especially at a time when DRAM scaling is becoming extremely complex,” the company says. “Being first to market strongly positions us to continue offering high-value solutions across a wide portfolio of end customer applications.”

According to Micron, 1z nm memory products deliver "substantially higher" bit density, "significant" performance enhancements and lower costs compared to the previous generation 1Y nm mode. As such, it should deliver improvements for compute DRAM (DDR4), mobile DRAM (LPDDR4) and graphics DRAM (GDDR6) products. Products using the smaller node promise a 40% reduction in power consumption compared to previous generation 8Gb DDR4 memory, while addressing the growing need for more performance and higher density.

Micron Produces DRAM With 1z Nanometer Process

Written by Alice Marshall

21 August 2019

In addition, Micron starts volume shipments of its highest-capacity monolithic 16Gb LPDDR4X DRAM in UFS-based multichip packages (uMCP4). It says the 1z nm LPDDR4X and uMCP4 address the needs of mobile device manufacturers seeking low power and smaller packages to design devices with both attractive form factors and long battery life.

Go [Micron Commences Volume Production of 1z Nanometer DRAM Process Node](#)